



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Note 9)
60V	$3.65 \text{m}\Omega$ @ V _{GS} = 10V	100A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

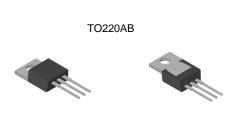
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

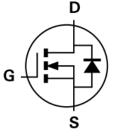
 https://www.diodes.com/quality/product-definitions/

Mechanical Data

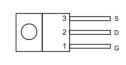
- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (2)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







Equivalent Circuit



Top View Pin Out Configuration

Ordering Information (Note 4)

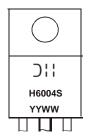
Part Number	Case	Packaging
DMTH6004SCT	TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Bottom View

Marking Information



The Manufacturer's Marking
H6004S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Notes 6 & 9)	Tc = +25°C	ID	100	А
Continuous Diam Current (Notes 6 & 9)	$T_{C} = +100^{\circ}C$		100	
Maximum Continuous Body Diode Forward Current (Notes 6 & 9)	Tc = +25°C	Is	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	lрм	180	Α	
Avalanche Current, L=0.2mH	las	45	Α	
Avalanche Energy, L=0.2mH	Eas	200	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	52.8	°C/W
Total Power Dissipation (Note 6)	$T_C = +25$ °C	P _D	136	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1.1	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

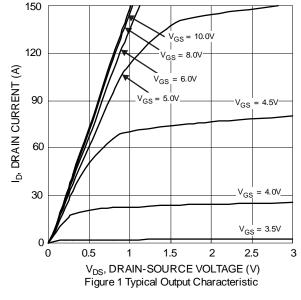
Electrical Characteristics ($@T_A = +25$ °C, unless otherwise specified.)

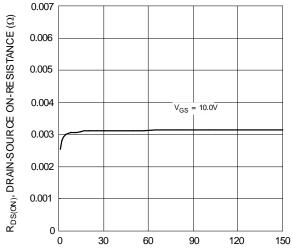
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	3.1	3.65	mΩ	V _G S = 10V, I _D =100A	
Diode Forward Voltage	V_{SD}	_	_	1.3	V	$V_{GS} = 0V, I_{S} = 100A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	4,556			$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	1,383	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	105	_			
Gate Resistance	R _G	_	0.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{G}	_	95.4	_		V _{DD} = 30V, I _D = 90A, V _{GS} = 10V	
Gate-Source Charge	Qgs	_	21.6	_	nC		
Gate-Drain Charge	Q _{GD}	_	20.4			VGS - 10V	
Turn-On Delay Time	td(ON)		14.3	_		$V_{DD} = 30V$, $V_{GS} = 10V$, $I_{D} = 90A$, $R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	99.1		ns		
Turn-Off Delay Time	t _{D(OFF)}	_	40	_	110		
Turn-Off Fall Time	t _F	_	17.6	_			
Reverse Recovery Time	t _{RR}	_	50.5	_	ns	L 400 di/dt 4000/	
Reverse Recovery Charge	Qrr	_	80.8	_	nC	- I _F = 48A, di/dt = 100A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

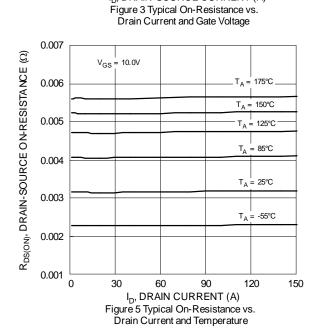
- Device mounted on infinite heat sink.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.
- 9. Package limited.

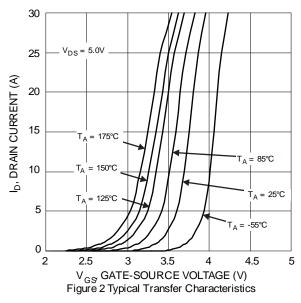


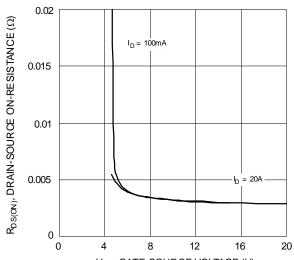




I_D, DRAIN-SOURCE CURRENT (A)







V_{GS} GATE-SOURCE VOLTAGE (V) Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

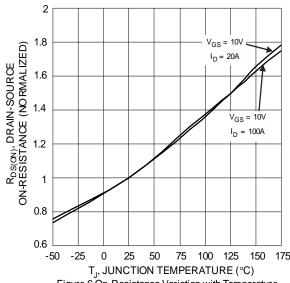
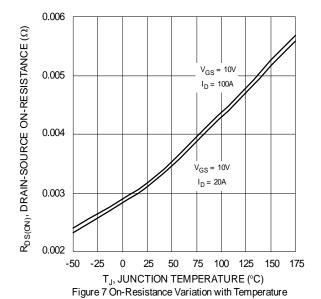
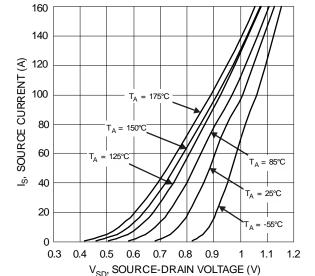
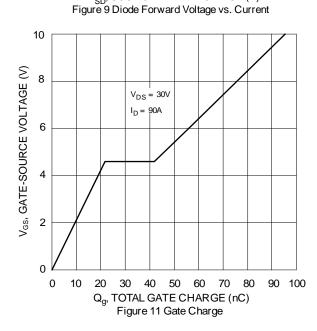


Figure 6 On-Resistance Variation with Temperature









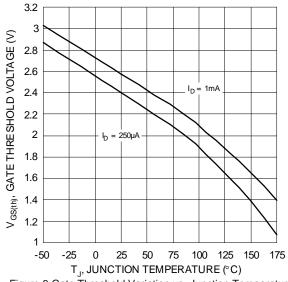
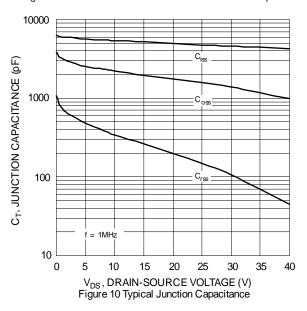
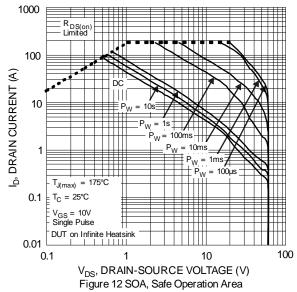
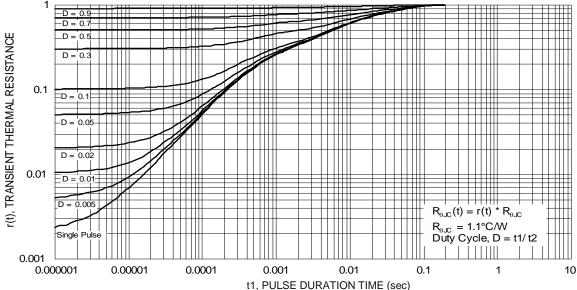


Figure 8 Gate Threshold Variation vs. Junction Temperature







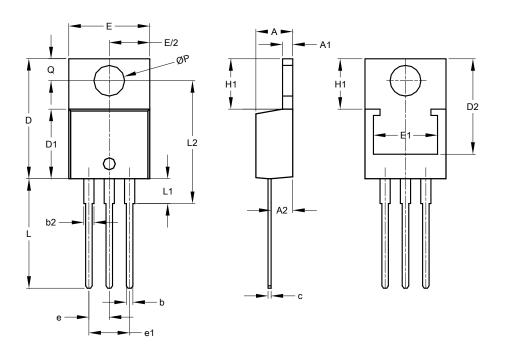




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



TO220AB					
Dim	Min	Max	Тур		
Α	3.56	4.82	-		
A1	0.51	1.39	-		
A2	2.04	2.92	-		
b	0.39	1.01	0.81		
b2	1.15	1.77	1.24		
С	0.356	0.61	-		
D	14.22	16.51	-		
D1	8.39	9.01	-		
D2	11.45	12.87	-		
е	-	-	2.54		
e1	-	-	5.08		
Ε	9.66	10.66	-		
E1	6.86	8.89	-		
H1	5.85	6.85	-		
J	12.70	14.73	-		
L1	-	4.42	-		
L2	15.80	17.51	16.00		
Р	3.54	4.08	-		
Q	2.54	3.42	-		
All Dimensions in mm					



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